

JST20A-800CW 20A TRIAC

Rev.A.1.1

DESCRIPTION:

The J J.- T

Average gate power dissipation ( $T_j=125$ )	$P_{G(AV)}$	0.5	W
Peak gate power	$P_{GM}$	10	W
Peak pulse voltage ( $T_j=25$ ; non-repetitive,off-state;FIG.7)	$V_{pp}$	4	kV

## ELECTRICAL CHARACTERISTICS (unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	35	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=125$ $R_L=3.3k$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	50	mA
				60	
$I_H$	$I_T=500mA$		MAX.	40	mA
$dV/dt$	$V_D=540V$ Gate Open $T_j=125$		MIN.	1600	V/s
$(dI/dt)_c$	$G9 GWF j=125V 7$		MIN.	20	A/ms
$t_{on}$	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	7	s
$t_{off}$				50	

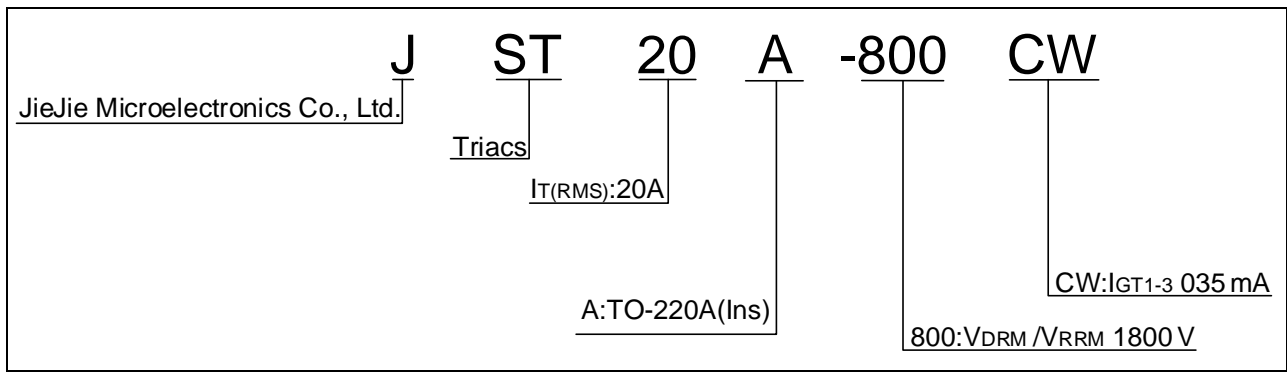
## STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=28A t_p=380$ s	$T_j=25$	1.4	V
$V_{TO}$	Threshold voltage	$T_j=125$	0.75	V
$R_D$	Dynamic resistance	$T_j=125$	20	P
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	A
$I_{RRM}$		$T_j=125$	1	mA

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.9	/W
$R_{th(j-a)}$	junction to ambient (AC)	60	/W

ORDERING INFORMATION



MARKING

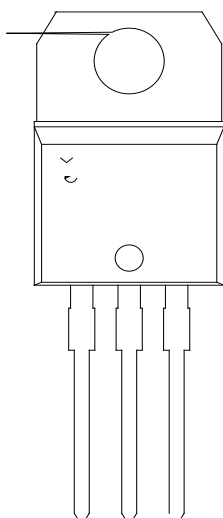


FIG.1: Maximum power dissipation versus RMS on-state current

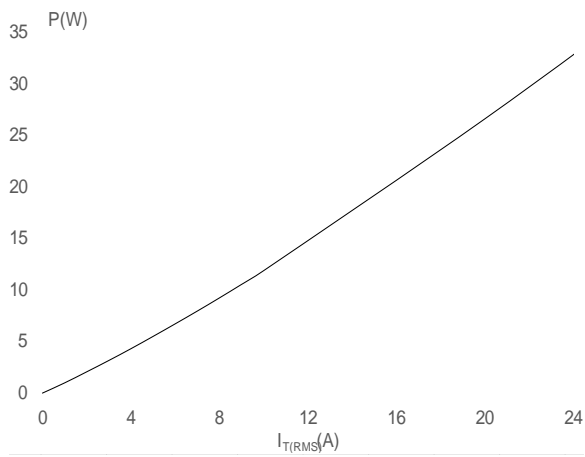


FIG.2: RMS on-state current versus case temperature

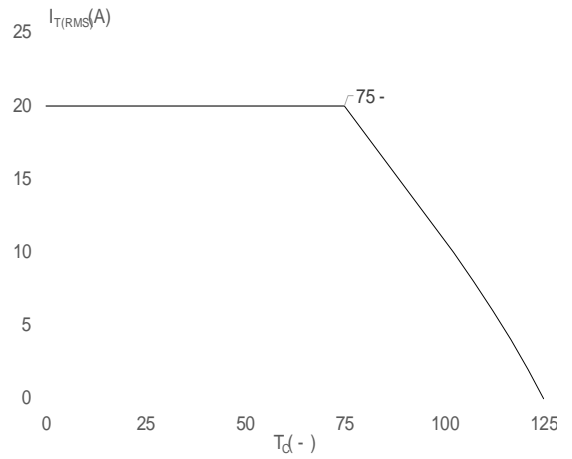


FIG.3: Surge peak on-state current versus number of cycles

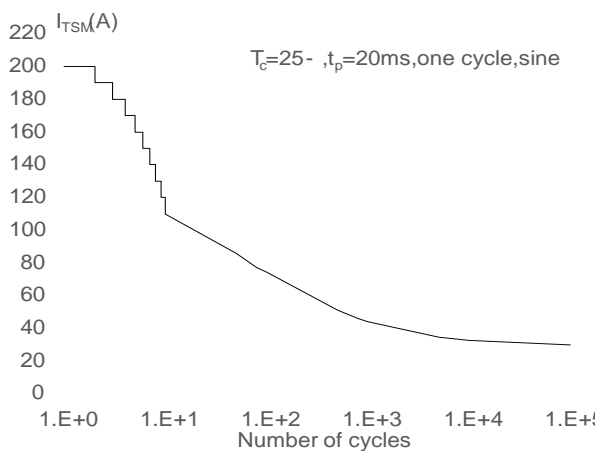
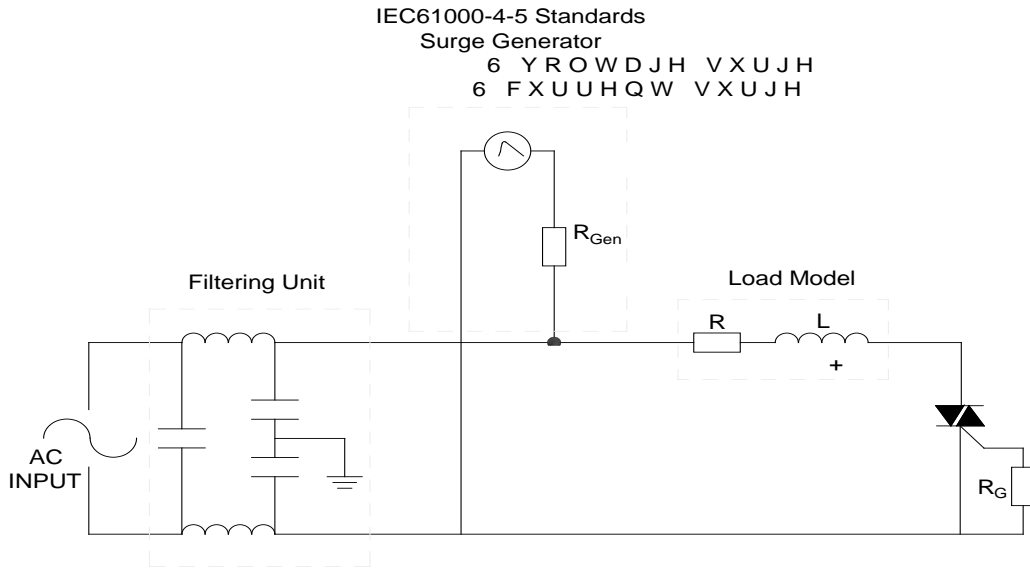


FIG.4: On-state characteristics

FIG.7 ÖTest circuit for inductive and resistive loads to IEC-61000-4-5 standards





PACKAGE MECHANICAL DATA

